Nathan Newman

List of Publications by Year
in descending order

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142	5,004	87723	102304
papers	citations	38 h-index	66 g-index

152	152	152	3551
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Effect of heat treatment on the properties of non-stoichiometric Ba3CoNb2O9 ceramics: Evaluation of crystal structure, order-disorder behavior, and dielectric characteristics. Journal of the European Ceramic Society, 2022, 42, 3224-3224.	2.8	2
2	Working with Frank Wilczek to Make the Invisible, Visible. , 2022, , 181-184.		0
3	Development of magnetically switchable high permittivity microwave dielectrics using La(Al_{1â€x}Fe_x)O₃. Journal of the American Ceramic Society, 2021, 104, 2669-2677.	1.9	0
4	First principles study of phase stability in Ba-based tantalate complex double perovskites. Applied Physics Letters, 2021, 119, 052901.	1.5	1
5	Low microwave loss in deposited Si and Ge thin-film dielectrics at single-photon power and low temperatures. AIP Advances, 2021, 11, .	0.6	2
6	Low-temperature synthesis of 2D anisotropic MoTe2 using a high-pressure soft sputtering technique. Nanoscale Advances, 2020, 2, 1443-1448.	2.2	5
7	Magnetically tuning the loss tangent in La(Al1â^'xFex)O3 using low field electron paramagnetic resonance transitions. Applied Physics Letters, 2020, 117, 222901.	1.5	2
8	Influence of substrate temperature on properties of pyrite thin films deposited using a sequential coevaporation technique. Thin Solid Films, 2019, 669, 49-55.	0.8	5
9	Clean to dirty limit andT_csuppression in NdFeAsO_{0.7}F_{0.3}studied byH_{c2}analysis. Superconductor Science and Technology, 2018, 31, 034007.	1.8	4
10	Effect ofÎ±-particle irradiation on a NdFeAs(O,F) thin film. Superconductor Science and Technology, 2018, 31, 034002.	1.8	7
11	Improvement in the Magnetic Properties of Niâ€“Fe Thin Films on Thick Nb Electrodes Using Oxidation and Low-Energy Ar Ion Milling. IEEE Magnetics Letters, 2018, 9, 1-4.	0.6	1
12	Magnetic properties of chromium-doped Ni80Fe20 thin films. Journal of Magnetism and Magnetic Materials, 2018, 460, 193-202.	1.0	7
13	Large Uniaxial Anisotropy Induced in Soft Ferromagnetic Thin Films by Oblique Deposition of Underlayer. IEEE Magnetics Letters, 2018, 9, 1-5.	0.6	1
14	Origin of dielectric loss in Ba(Co_{1/3}Nb_{2/3})O₃ microwave ceramics. Journal of the American Ceramic Society, 2018, 101, 1665-1676.	1.9	15
15	Better Resolution of High-Spin Cobalt Hyperfine at Low Frequency: Co-Doped Ba(Zn1/3Ta2/3)O3 as a Model Complex. International Journal of Molecular Sciences, 2018, 19, 3532.	1.8	4
16	Switching microwave dielectric resonators from a high-Q on state to an off state using low-field electron paramagnetic resonance transitions. Applied Physics Letters, 2018, 113, .	1.5	4
17	Fundamental mechanisms responsible for the temperature coefficient of resonant frequency in microwave dielectric ceramics. Journal of the American Ceramic Society, 2017, 100, 1508-1516.	1.9	16
18	Effect of non-stoichiometry on the densification, phase purity, microstructure, crystal structure, and dielectric loss of Ba(Co 1/3 Nb 2/3)O 3 ceramics. Journal of the European Ceramic Society, 2017, 37, 3335-3346.	2.8	9

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19	The magnetic, electrical and structural properties of copper-permalloy alloys. Journal of Magnetism and Magnetic Materials, 2017, 442, 45-52.	1.0	11
20	In-situ electron paramagnetic resonance studies of paramagnetic point defects in superconducting microwave resonators. Applied Physics Letters, 2016, 109, .	1.5	2
21	Nanoporous Delafossite CuAlO₂ from Inorganic/Polymer Double Gels: A Desirable High-Surface-Area p-Type Transparent Electrode Material. Inorganic Chemistry, 2015, 54, 1100-1108.	1.9	20
22	Main Source of Microwave Loss in Transitionâ€Metalâ€Doped Ba(Zn_{1/3}Ta_{2/3})O₃ and Ba(Zn_{1/3}Nb_{2/3})O₃ at Cryogenic Temperatures. Journal of the American Ceramic Society, 2015, 98, 1188-1194.	1.9	17
23	Kinetic Processes in Vapor PhaseÂEpitaxy. , 2015, , 835-868.		1
24	Fabrication of highly spin-polarized Co2FeAl0.5Si0.5 thin-films. APL Materials, 2014, 2, .	2.2	12
25	Electromagnetic bandgap resonators synthesized using ceramic injection molding. Microwave and Optical Technology Letters, 2014, 56, 371-375.	0.9	0
26	High Energy and Spatial Resolution EELS Band Gap Measurements Using a Nion Monochromated Cold Field Emission HERMES Dedicated STEM. Microscopy and Microanalysis, 2014, 20, 70-71.	0.2	2
27	Switching at small magnetic fields in Josephson junctions fabricated with ferromagnetic barrier layers. Applied Physics Letters, 2014, 104, .	1.5	49
28	Growth and characterization of epitaxial Ba(Co,Zn)1/3Nb2/3O3 thin films. Journal of Crystal Growth, 2014, 387, 81-85.	0.7	2
29	Criteria for improving the properties of ZnGeAs₂ solar cells. Progress in Photovoltaics: Research and Applications, 2013, 21, 906-917.	4.4	13
30	Growth of epitaxial pyrite (FeS2) thin films using sequential evaporation. Acta Materialia, 2013, 61, 7392-7398.	3.8	8
31	Effect of Helium Ion Irradiation on the Tunneling Behavior in Niobium/Aluminumâ€“Aluminum Oxide/Niobium Josephson Junctions. IEEE Transactions on Applied Superconductivity, 2013, 23, 1101610-1101610.	1.1	1
32	Structural, electrical, and thermoelectric properties of CrSi 2 thin films. Thin Solid Films, 2013, 545, 100-105.	0.8	6
33	Investigations of the disorder in the TaxN thin films: On the first order Raman spectrum of the rock salt crystal structure. Journal of Applied Physics, 2013, 114, .	1.1	5
34	The Southwestern Center for Aberration Corrected Electron Microscopy at Arizona State University: The Facility. Microscopy and Microanalysis, 2012, 18, 408-409.	0.2	1
35	Microwave Loss in the High-Performance Dielectric<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>Ba</mml:mi><mml:mo stretchy="false">(</mml:mo><mml:msub><mml:mi>Zn</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>/</mml:mo><mml:mn>3</mml:mn></mml:mrow></mml:msub><mml:msub><mml:mi mathvariant="bold">O</mml:mi><mml:mn>3</mml:mn></mml:msub>	2.9	29
36	Thermoelectric properties of Zn5Sb4In2-Î´ (Î´â€‰=â€‰0.15). Journal of Applied Physics, 2012, 111, 123712.	1.1	5

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37	The dominance of paramagnetic loss in microwave dielectric ceramics at cryogenic temperatures. Applied Physics Letters, 2012, 101, .	1.5	18
38	Defect energy levels and electronic behavior of Ni-, Co-, and As-doped synthetic pyrite (FeS2). Journal of Applied Physics, 2012, 111, .	1.1	38
39	Experimental study of the kinetically-limited decomposition of ZnGeAs2 and its role in determining optimal conditions for thin film growth. Journal of Crystal Growth, 2012, 338, 267-271.	0.7	1
40	Growth and characterization of Ba(Cd1/3Ta2/3)O3 thin films. Thin Solid Films, 2012, 520, 6153-6157.	0.8	6
41	One-pot synthesis of highly mesoporous antimony-doped tin oxide from interpenetrating inorganic/organic networks. Journal of Materials Chemistry, 2011, 21, 13232.	6.7	39
42	Electrical properties of AsxSe1âˆ’x (xâ‰¤0.05) Mott-barriers. Journal of Non-Crystalline Solids, 2011, 357, 3366-3372.	1.5	4
43	Effects of stress on phase separation in InxGa1âˆ’xN/GaN multiple quantum-wells. Acta Materialia, 2011, 59, 3759-3769.	3.8	15
44	Influence of surface topography on in situ reflection electron energy loss spectroscopy plasmon spectra of AlN, GaN, and InN semiconductors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2011, 29, .	0.9	7
45	Electrical conductivities and Li ion concentration-dependent diffusivities, in polyurethane polymers doped with lithium trifluoromethanesulfonimide (LiTFSI) or lithium perchlorate (LiClO4). Solid State Ionics, 2010, 181, 1727-1731.	1.3	14
46	Characterization of Josephson and quasi-particle currents in MgB2/MgB2and Pb/Pb contact junctions. Superconductor Science and Technology, 2010, 23, 075003.	1.8	7
47	Nanoscale disorder in pure and doped MgB₂thin films. Superconductor Science and Technology, 2010, 23, 095008.	1.8	13
48	Thin film tandem photovoltaic cell from II-IV-V chalcopyrites. Applied Physics Letters, 2010, 96, 143503.	1.5	18
49	Low-temperature transport properties of Ta_xN thin films (0.72 â©½ x â©½ 0.83). Journal Physics D: Applied Physics, 2010, 43, 445405.	1.3	3
50	Suppression of the Critical Temperature of Superconducting NdFeAs(OF) Single Crystals by Kondo-Like Defect Sites Induced by<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>Î±</mml:mi></mml:math>-Particle Irradiation. Physical Review Letters, 2010, 104, 087002.	2.9	70
51	Cd13âˆ’xInySb10(xâ‰ˆ2.7,yâ‰ˆ1.5): An Interstitial-Free Variant of Thermoelectric Î²-Zn4Sb3. Chemistry - A European Journal, 2009, 15, 6704-6710.	1.7	4
52	Leakage-current characteristics of vanadium- and scandium-doped barium strontium titanate ceramics over a wide range of DC electric fields. Acta Materialia, 2009, 57, 4935-4947.	3.8	11
53	Metalâ€“nonmetal transition in the sphalerite-type solid solution [ZnSnSb2]1âˆ’x[2(InSb)]x. Journal of Solid State Chemistry, 2009, 182, 1438-1442.	1.4	5
54	Growth and characterization of epitaxial Ba(Zn1/3Ta2/3)O3 (100) thin films. Acta Materialia, 2009, 57, 432-440.	3.8	26

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55	Zn5Sb4In2â˜Î´ â€" a Ternary Derivative of Thermoelectric Zinc Antimonides. Inorganic Chemistry, 2009, 48, 5996-6003.	1.9	7
56	Large magnetoresistance of thick polymer devices having La0.67Sr0.33MnO3 electrodes. Applied Physics Letters, 2009, 95, .	1.5	15
57	Comparative Study of the Thermoelectric Properties of Amorphous Zn₄₁Sb₅₉ and Crystalline Zn₄Sb₃. Chemistry of Materials, 2009, 21, 151-155.	3.2	41
58	Stacking faults in quaternary In Al Ga1â˜'â˜'N layers. Acta Materialia, 2008, 56, 4036-4045.	3.8	17
59	Phase separation and atomic ordering in InxAlyGa1â˜'xâ˜'yN layers. Acta Materialia, 2008, 56, 5552-5559.	3.8	12
60	Metastable Cd4Sb3: A Complex Structured Intermetallic Compound with Semiconductor Properties. Journal of the American Chemical Society, 2008, 130, 15564-15572.	6.6	24
61	[0001] composition modulations in Al0.4Ga0.6N layers grown by molecular beam epitaxy. Applied Physics Letters, 2008, 92, 261914.	1.5	12
62	Effect of oxygen incorporation on normal and superconducting properties of MgB2 films. Applied Physics Letters, 2008, 93, 242504.	1.5	11
63	Saturation and intrinsic dynamics of fluxons in NbTi and MgB2. Applied Physics Letters, 2007, 90, 132504.	1.5	1
64	Low-Temperature Structural Transitions in the Phonon-Glass Thermoelectric Material Î²-Zn4Sb3:Â Ordering of Zn Interstitials and Defects. Chemistry of Materials, 2007, 19, 834-838.	3.2	89
65	Structureâ€"dielectric property relationship for vanadium- and scandium-doped barium strontium titanate. Acta Materialia, 2007, 55, 2647-2657.	3.8	22
66	Effect of metal doping on the low-temperature structural behavior of thermoelectric Î²-Zn4Sb3. Journal of Solid State Chemistry, 2007, 180, 2603-2615.	1.4	57
67	Atomic Resolution Transmission Electron Microscopy of the Microstructure of Ordered Ba(Cd1/3Ta2/3)O3 Perovskite Ceramics. Journal of the American Ceramic Society, 2006, 89, 1047-1052.	1.9	10
68	Structural, chemical and dielectric properties of ceramic injection moulded Ba(Zn1/3Ta2/3)O3 microwave dielectric ceramics. Journal of the European Ceramic Society, 2006, 26, 3273-3278.	2.8	6
69	Internally shunted Josephson junctions with barriers tuned near the metalâ€"insulator transition for RSFQ logic applications. Superconductor Science and Technology, 2006, 19, 719-731.	1.8	21
70	Structural, Dielectric, and Optical Properties of Ni-Doped Barium Cadmium Tantalate Ceramics. Japanese Journal of Applied Physics, 2006, 45, 9140-9142.	0.8	3
71	Electrical transport properties of ferromagnetic GaxCr1â˜'xN thin films. Applied Physics Letters, 2006, 89, 142105.	1.5	13
72	Role of Embedded Clustering in Dilute Magnetic Semiconductors: Cr Doped GaN. Physical Review Letters, 2005, 95, 256404.	2.9	212

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73	Half-Metallicity and Efficient Spin Injection inAlN/GaNâˆ¶Cr(0001) Heterostructure. Physical Review Letters, 2005, 94, 146602.	2.9	41
74	Incorporation of a Frequency-Dependent Dielectric Response for the Barrier Material in the Josephson Junction Circuit Model. IEEE Transactions on Applied Superconductivity, 2005, 15, 3886-3900.	1.1	5
75	Fabrication of Niobium Titanium Nitride Thin Films With High Superconducting Transition Temperatures and Short Penetration Lengths. IEEE Transactions on Applied Superconductivity, 2005, 15, 44-48.	1.1	23
76	Observation of ferromagnetism above 900K in Crâ€“GaN and Crâ€“AlN. Applied Physics Letters, 2004, 85, 4076-4078.	1.5	207
77	Ordered domains and boundary structure in Ba(Cd1/3Ta2/3)O3 perovskite dielectrics. Applied Physics Letters, 2004, 84, 3918-3920.	1.5	14
78	Microstructure and dielectric properties of Ba(Cd1/3Ta2/3)O3 microwave ceramics synthesized with a boron oxide sintering aid. Journal of Materials Research, 2004, 19, 3526-3533.	1.2	12
79	Electron microscopy characterization of Ba(Cd1/3Ta2/3)O3 microwave dielectrics with boron additive. Journal of Materials Research, 2004, 19, 1387-1391.	1.2	6
80	Thermochemical analysis of MgB2 synthesis by molecular-beam epitaxy. Journal of Crystal Growth, 2004, 270, 107-112.	0.7	15
81	Spin lifetimes of electrons injected into GaAs and GaN. Applied Physics Letters, 2003, 83, 1761-1763.	1.5	109
82	Thermochemistry of MgB/sub 2/ thin film synthesis. IEEE Transactions on Applied Superconductivity, 2003, 13, 3238-3241.	1.1	57
83	Synthesis, characterization, and modeling of high quality ferromagnetic Cr-doped AlN thin films. Applied Physics Letters, 2003, 82, 3047-3049.	1.5	166
84	Theoretical and Experimental Study of Barium Zinc-Cadmium Tantalate-based Microwave Dielectrics. Materials Research Society Symposia Proceedings, 2003, 783, 471.	0.1	1
85	Measurement of the coherence length of sputtered Nb/sub 0.62/Ti/sub 0.38/N thin films. IEEE Transactions on Applied Superconductivity, 2002, 12, 1795-1798.	1.1	12
86	Experimental determination of the rates of decomposition and cation desorption from AlN surfaces. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 87, 244-248.	1.7	36
87	Bandpass filters using dual-mode and quad-mode Mobius resonators. IEEE Transactions on Microwave Theory and Techniques, 2001, 49, 2363-2368.	2.9	16
88	Internally shunted sputtered NbN Josephson junctions with a TaNx barrier for nonlatching logic applications. Applied Physics Letters, 2001, 78, 99-101.	1.5	62
89	Experimental study of MgB2 decomposition. Applied Physics Letters, 2001, 79, 87-89.	1.5	82
90	Defect annihilation in AlN thin films by ultrahigh temperature processing. Applied Physics Letters, 2000, 76, 1839-1841.	1.5	35

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91	Role of Ni and Zr doping on the electrical, optical, magnetic, and structural properties of barium zinc tantalate ceramics. Journal of Materials Research, 1999, 14, 4011-4019.	1.2	35
92	High temperature growth of AlN by plasma-enhanced molecular beam epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 67, 80-87.	1.7	25
93	Control of the structure and surface morphology of gallium nitride and aluminum nitride thin films by nitrogen background pressure in pulsed laser deposition. Journal of Electronic Materials, 1998, 27, 215-221.	1.0	15
94	Influence of the exchange reaction on the electronic structure of GaN/Al junctions. Physical Review B, 1998, 58, 7906-7912.	1.1	11
95	Precise control of atomic nitrogen production in an electron cyclotron resonance plasma using N2/noble gas mixtures. Applied Physics Letters, 1998, 73, 456-458.	1.5	23
96	The energetics of the GaN MBE reaction: a case study of meta-stable growth. Journal of Crystal Growth, 1997, 178, 102-112.	0.7	65
97	Hollowâ€anode plasma source for molecular beam epitaxy of gallium nitride. Review of Scientific Instruments, 1996, 67, 905-907.	0.6	34
98	Homoepitaxial growth of GaN using molecular beam epitaxy. Journal of Applied Physics, 1996, 80, 2195-2198.	1.1	35
99	Thermal annealing characteristics of Si and Mgâ€implanted GaN thin films. Applied Physics Letters, 1996, 68, 2702-2704.	1.5	43
100	The influence of nitrogen ion energy on the quality of GaN films grown with molecular beam epitaxy. Journal of Electronic Materials, 1995, 24, 249-255.	1.0	33
101	Experimental determination of the pressure dependence of the barrier height of metal/[n-type GaAs] Schottky contacts: A critical test of Schottky-barrier models. Physical Review B, 1995, 51, 18003-18006.	1.1	15
102	Electron microscopy characterization of GaN films grown by molecular-beam epitaxy on sapphire and SiC. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 1578.	1.6	69
103	Pressure Dependence of III-V Schottky Barriers: A Critical Test of Theories for Fermi Level Pinning. Physical Review Letters, 1994, 73, 581-584.	2.9	19
104	Observation of stimulated emission in the near ultraviolet from a molecular beam epitaxy grown GaN film on sapphire in a verticalâ€cavity, single pass configuration. Applied Physics Letters, 1994, 64, 1135-1137.	1.5	34
105	Scanning tunneling microscopy studies of Si donors (SiGa) in GaAs. Physical Review Letters, 1994, 72, 1490-1493.	2.9	193
106	High-temperature superconductive devices on sapphire. IEEE Transactions on Microwave Theory and Techniques, 1994, 42, 34-40.	2.9	27
107	pâ€type gallium nitride by reactive ionâ€beam molecular beam epitaxy with ion implantation, diffusion, or coevaporation of Mg. Applied Physics Letters, 1994, 64, 64-66.	1.5	167
108	1.54â€Î¼m photoluminescence from Erâ€implanted GaN and AlN. Applied Physics Letters, 1994, 65, 992-994.	1.5	197

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109	High-temperature superconducting microwave devices: Fundamental issues in materials, physics, and engineering. Journal of Superconductivity and Novel Magnetism, 1993, 6, 119-160.	0.5	167
110	First direct observation of EL2-like defect levels in annealed LT-GaAS. Journal of Electronic Materials, 1993, 22, 1499-1502.	1.0	20
111	Thermodynamic and kinetic processes involved in the growth of epitaxial GaN thin films. Applied Physics Letters, 1993, 62, 1242-1244.	1.5	82
112	Correspondence between microwave and submillimeter absorptivity in epitaxial thin films ofYBa2Cu3O7. Physical Review B, 1993, 47, 8076-8088.	1.1	23
113	Largeâ€area YBa2Cu3O7âˆ'Î´thin films on sapphire for microwave applications. Applied Physics Letters, 1992, 61, 1727-1729.	1.5	104
114	High temperature superconducting transresistance amplifiers for far infrared detectors. IEEE Transactions on Applied Superconductivity, 1992, 2, 111-113.	1.1	4
115	Submillimeter and microwave residual losses in epitaxial films of Y-Ba-Cu-O and Tl-Ca-Ba-Cu-O. Journal of Superconductivity and Novel Magnetism, 1992, 5, 379-388.	0.5	6
116	Fabrication and measurement of high T/sub c/ superconducting microbolometers. IEEE Transactions on Magnetics, 1991, 27, 3081-3084.	1.2	41
117	Biâ€epitaxial grain boundary junctions in YBa2Cu3O7. Applied Physics Letters, 1991, 59, 733-735.	1.5	299
118	High-temperature superconductor resonators and phase shifters. IEEE Transactions on Applied Superconductivity, 1991, 1, 58-66.	1.1	24
119	Double gun off-axis sputtering of large area YBa/sub 2/Cu/sub 3/O/sub 7- delta / superconducting films for microwave applications. IEEE Transactions on Magnetics, 1991, 27, 1276-1279.	1.2	57
120	Residual losses in epitaxial thin films of YBa2Cu3O7from microwave to submillimeter wave frequencies. Applied Physics Letters, 1991, 59, 2326-2328.	1.5	28
121	van Schilfgaarde and Newman reply. Physical Review Letters, 1991, 67, 282-282.	2.9	5
122	van Schilfgaarde and Newman reply. Physical Review Letters, 1991, 67, 2746-2746.	2.9	3
123	High critical current densities in epitaxial YBa2Cu3O7âˆ'Î´thin films on siliconâ€onâ€sapphire. Applied Physics Letters, 1991, 58, 2432-2434.	1.5	57
124	Observation of two inâ€plane epitaxial states in YBa2Cu3O7âˆ'Î´films on yttriaâ€stabilized ZrO2. Applied Physics Letters, 1991, 58, 2168-2170.	1.5	97
125	Electronic structure of ideal metal/GaAs contacts. Physical Review Letters, 1990, 65, 2728-2731.	2.9	52
126	Microwave surface resistance of epitaxial YBa2Cu3O7thin films on sapphire. Applied Physics Letters, 1990, 57, 409-411.	1.5	108

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127	YBa2Cu3O7â˜Î´superconducting films with low microwave surface resistance over large areas. Applied Physics Letters, 1990, 57, 520-522.	1.5	99
128	Influence of interfacial contamination on the structure and barrier height of Cr/GaAs Schottky contacts. Applied Physics Letters, 1989, 54, 356-358.	1.5	8
129	Mechanism for nearly ohmic behavior in annealed Au/nâ€GaAs Schottky diodes. Journal of Applied Physics, 1989, 66, 711-715.	1.1	6
130	Schottky barrier instabilities due to contamination. Applied Physics Letters, 1988, 53, 145-147.	1.5	20
131	Aging of Schottky diodes formed on airâ€exposed and atomically clean GaAs surfaces: An electrical study. Journal of Applied Physics, 1988, 63, 2006-2010.	1.1	13
132	Engineered Schottky barrier diodes for the modification and control of Schottky barrier heights. Journal of Applied Physics, 1987, 61, 5159-5169.	1.1	59
133	Electrical study of Schottky-barrier heights on atomically cleanp-type InP(110) surfaces. Physical Review B, 1987, 35, 6298-6304.	1.1	47
134	The mechanisms of Schottky barrier pinning in IIIâ€“V semiconductors: Criteria developed from microscopic (atomic level) and macroscopic experiments. Surface Science, 1986, 168, 240-259.	0.8	63
135	Morphology of Au/GaAs interfaces. Applied Physics Letters, 1986, 49, 1514-1516.	1.5	29
136	Electrical study of Schottky barriers on atomically clean GaAs(110) surfaces. Physical Review B, 1986, 33, 1146-1159.	1.1	140
137	Schottky barriers on atomically clean cleaved GaAs. Solid-State Electronics, 1985, 28, 307-312.	0.8	16
138	Electrical study of Schottky barrier heights on atomically clean and airâ€exposednâ€InP(110) surfaces. Applied Physics Letters, 1985, 46, 1176-1178.	1.5	82
139	Annealing of intimate Auâ€GaAs Schottky barriers: Thick and ultrathin metal films. Journal of Applied Physics, 1985, 57, 1247-1251.	1.1	30
140	Electronic properties of metal/IIIâ€“V semiconductor interfaces. Surface Science, 1985, 162, 591-604.	0.8	10
141	Electronic structure and Schottky-barrier formation of Ag onn-type GaAs(110). Physical Review B, 1985, 32, 918-923.	1.1	39
142	Aluminum Schottky barrier formation on arsenic capped and heat cleaned MBE GaAs(100). Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1984, 2, 481.	1.6	16